

1. Material Substrate GaAlAs (P Type) Removed
Epitaxial Layer GaAlAs (N/P Type)

2. Electrode N(Cathode) Side Gold Alloy
P(Anode) Side Gold Alloy

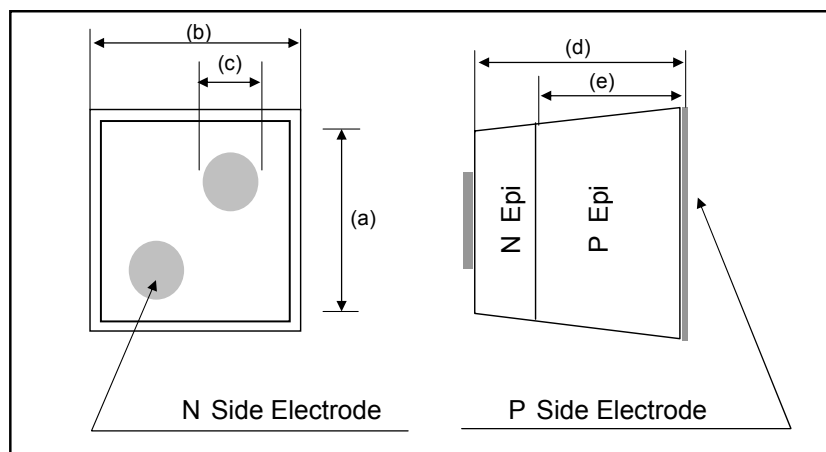
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.1		V	IF=10uA
	$V_{F(2)}$			1.6	V	IF=100mA
Reverse Voltage	V_R	5			V	IR=10uA
Power	P_O		1.65		mW	IF=50mA
Wavelength	λ_P		880		nm	IF=20mA
	$\Delta\lambda$		80		nm	IF=20mA
Rise Time	T_r		700		ns	
Fall Time	T_f		400		ns	

※ Note : LED chip is mounted on TO-18 gold header without resin coating.

4. Mechanical Data

- (a) Emission Area ----- 17.5mil x 17.5mil
- (b) Bottom Area ----- 18.5mil x 18.5mil
- (c) Bonding Pad ----- double pad
- (d) Chip Thickness ----- 10mil
- (e) Junction Height ----- 9.0mil



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